

# **Session WE3C**

## **Active Device Modeling**

**Chairman:**

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TRW

**Co-Chairman:**

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This session provides novel active parameter extraction and modeling techniques for small and large signal models. Two papers present bias and temperature dependence of the equivalent circuit parameters. The final paper presents scaling of HBT device models.

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**1:30 p.m.–3:00 p.m., Wednesday, May 17, 1995**  
**Room 12A,B,C**